



#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C	
100V	140mΩ @ $V_{GS} = 10V$	12A	
1007	160mΩ @ $V_{GS} = 4.5V$	11A	

## **Description**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

# **Applications**

- DC-DC Converters
- Power Management Functions
- Analog Switch

#### **Features**

- Low On-Resistance
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

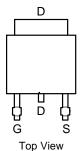
#### **Mechanical Data**

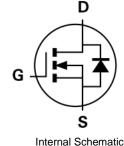
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 <sup>®</sup>
- Weight: 0.33 grams (Approximate)

#### TO252 (DPAK)



Top View





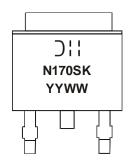
**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMN10H170SK3-13	TO252 (DPAK)	2.500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

# **Marking Information**



⊃ ¦ ¦ =Manufacturer's Marking
 N170SK= Product Type Marking Code
 YYWW = Date Code Marking
 YY=Last Digit of Year (ex: 15 = 2015)
 WW=Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	$V_{DSS}$	100	V		
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	I <sub>D</sub>	12 7.5	А		
Maximum Body Diode Forward Current (Note 5)	Is	4	Α		
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	16	Α		
Avalanche Current (Note 6)			I <sub>AS</sub>	5.3	Α
Avalanche Energy (Note 6)	E <sub>AS</sub>	20	mJ		

# **Thermal Characteristics**

Characteristic	Symbol	Value	Units	
Total Dower Discipation (Note 5)	$T_C = +25$ °C	C	42	W
Total Power Dissipation (Note 5)	T <sub>C</sub> = +100°C	$P_{D}$	17	
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	44	°C/W	
Thermal Resistance, Junction to Case (Note 5)	R <sub>0JC</sub>	3	*C/vv	
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	2.0	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	99	140	m0	$V_{GS} = 10V, I_D = 5A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	104	160	mΩ	$V_{GS} = 4.5V, I_D = 5A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 10A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		1,167			V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss		36		pF		
Reverse Transfer Capacitance	Crss		25	_			
Gate Resistance	$R_G$	_	1.3	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	4.9	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	9.7		nC	V <sub>DS</sub> = 80V, I <sub>D</sub> = 12.8A	
Gate-Source Charge	Qgs	_	2.0	_	IIC		
Gate-Drain Charge	$Q_{gd}$	_	2.0	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	10.5	_		$V_{DD} = 50V$ , $R_G = 25\Omega$ , $I_D = 12.8A$	
Turn-On Rise Time	tr	_	11.1	_	nS		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	42.6	_	113		
Turn-Off Fall Time	t <sub>f</sub>	_	12.8	_			
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	30.3		nS	$V_{GS} = 0V$ , $I_{S} = 12.8A$ , $dI/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge	$Q_{rr}$	_	35.2		nC	$V_{GS} = 0V$ , $I_S = 12.8A$ , $dI/dt = 100A/\mu s$	

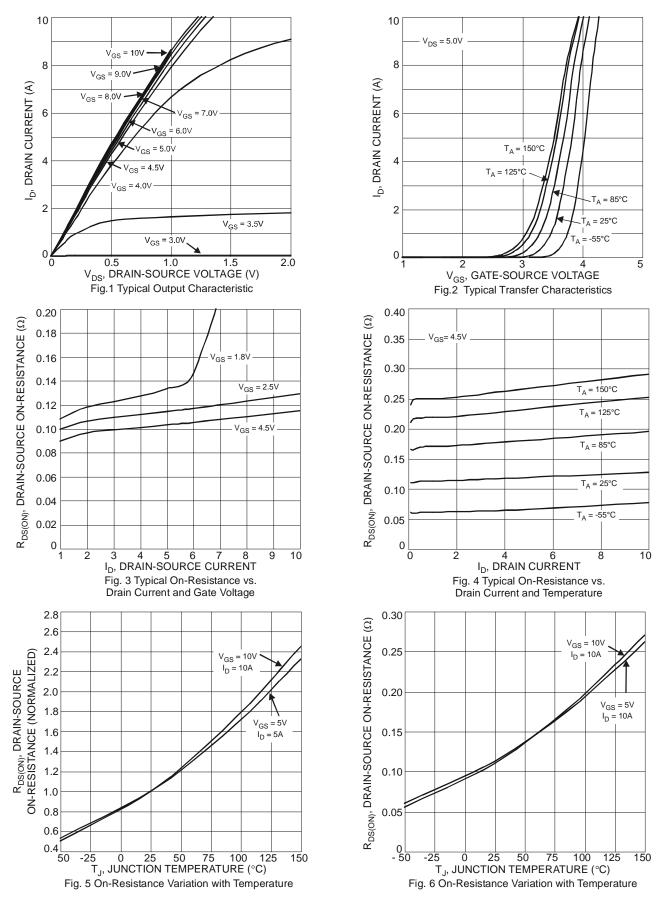
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper pad layout.

<sup>6.</sup> UIS in production with L = 1.43mH,  $T_J = +25$ °C.

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>8.</sup> Guaranteed by design; not subject to production testing.







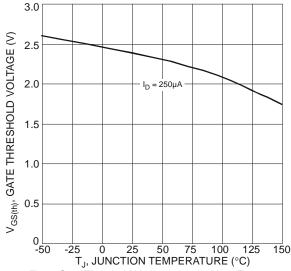


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

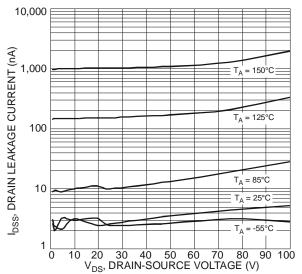
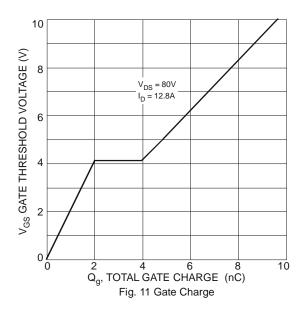
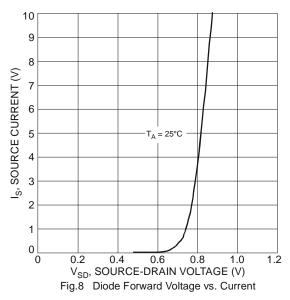
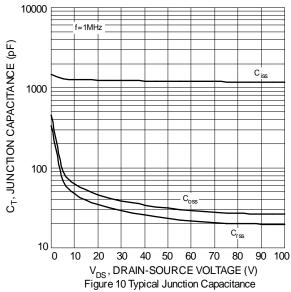
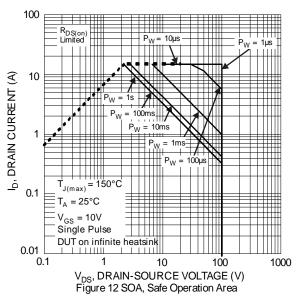


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

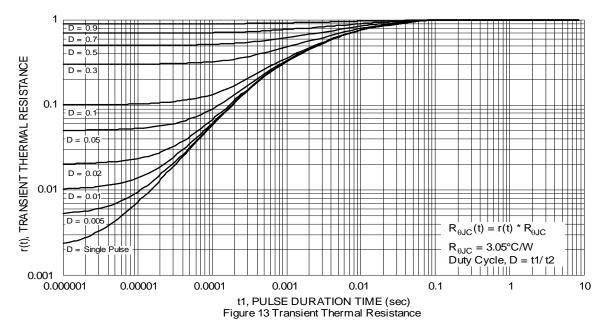










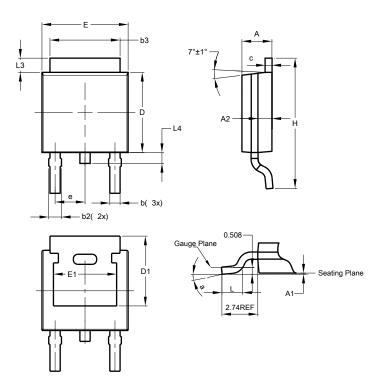




# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### TO252 (DPAK)

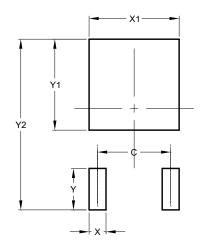


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
U	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	1			
e	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

#### TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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